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type data in specification

View Online at https://aerobasegroup.com/nsn/5961-00-479-7900

Inclosure Material:
Metal
Overall Length:
1.253 inches
End Application:
Aircraft; radar; fire control system; sonar acoustic miscellaneous;
Mounting Facility Quantity:
1
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Overall Width Across Flats:
Between 0.423 inches and 0.438 inches
Thread Size:
0.190 inches
Criticality Code Justification:
Feat
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
150.0 regulator voltage
Voltage Tolerance In Percent:
-5.0/+5.0
Current Rating Per Characteristic:
17.00 milliamperes source cutoff current horsepower metric and 62.00 milliamperes repetitive peak forward current
Power Rating Per Characteristic:
10.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction
Special Features:
Weapon system essential
Precious Material And Location:
Terminal surface option gold
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 1 tab, solder lug
Specification Data:
81349-mil-s-19500/124 government specification

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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